

60V PNP SURFACE MOUNT SMALL SIGNAL TRANSISTOR IN SOT23
Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMBT2222A)
- Ideal for Low Power Amplification and Switching
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP capable (Note 4)**

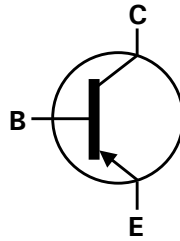
Mechanical Data

- Case: SOT23
- Case Material: molded Plastic, "Green" Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.008 grams (approximate)

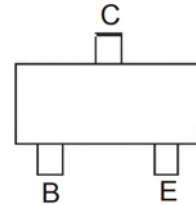


SOT23

Top View



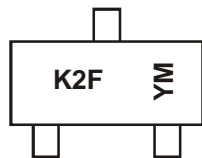
Device Symbol


 Top View
Pin-Out

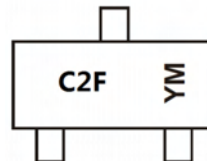
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT2907A-7-F	AEC-Q101	K2F / C2F	7	8	3,000
MMBT2907A-13-F	AEC-Q101	K2F / C2F	13	8	10,000
MMBT2907AQ-7-F	Automotive	K2F	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
 5. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information


K = SAT (Shanghai Assembly / Test site)
 2F = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)



C = CAT (Chengdu Assembly / Test site)
 2F = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017
Code	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

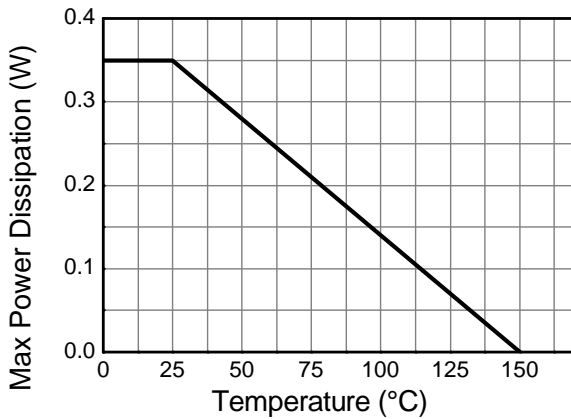
Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-600	mA
Peak Collector Current	I_{CM}	-800	mA

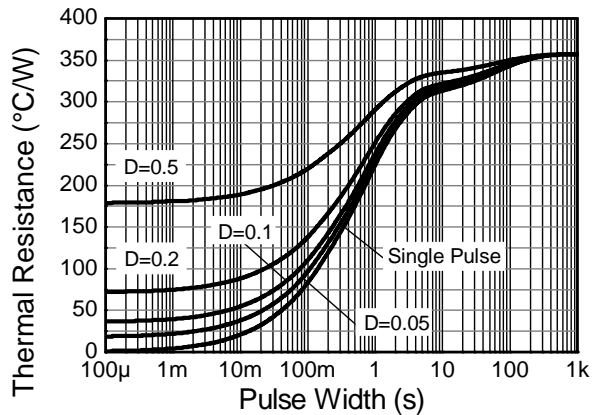
Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector Power Dissipation	P_D	310	mW
		350	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	403	$^\circ\text{C/W}$
		357	
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	350	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

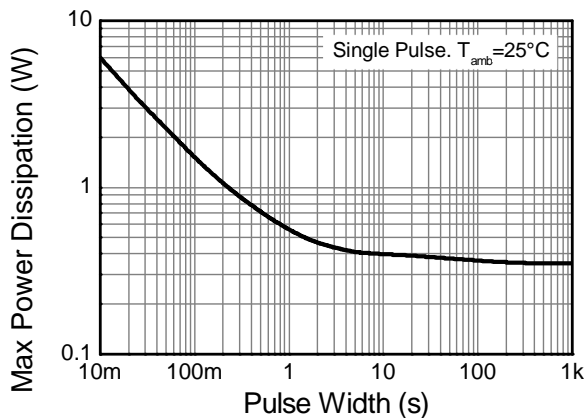
Notes: 6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition;
 7. Same as Note 5, expect the device is mounted on 15mm X 15mm X 1.6mm FR4 PCB
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)					
Collector-Base Breakdown Voltage	BV_{CBO}	-60	—	V	$I_C = -100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-60	—	V	$I_C = -10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5.0	—	V	$I_E = -100\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CBO}	—	-10	nA μA	$V_{CB} = -50\text{V}, I_E = 0$ $V_{CB} = -50\text{V}, I_E = 0, T_A = 125^\circ\text{C}$
Collector Cutoff Current	I_{CEX}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$
Base Cutoff Current	I_{BL}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h_{FE}	75	—	—	$I_C = -100\mu\text{A}, V_{CE} = -10\text{V}$ $I_C = -1.0\text{mA}, V_{CE} = -10\text{V}$ $I_C = -10\text{mA}, V_{CE} = -10\text{V}$ $I_C = -150\text{mA}, V_{CE} = -10\text{V}$ $I_C = -500\text{mA}, V_{CE} = -10\text{V}$
		100	—		
		100	—		
		100	300		
		50	—		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-0.4 -1.6	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	-1.3 -2.6	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	8.0	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	—	30	pF	$V_{EB} = -2.0\text{V}, f = 1.0\text{MHz}, I_C = 0$
Current Gain-Bandwidth Product	f_T	200	—	MHz	$V_{CE} = -20\text{V}, I_C = -50\text{mA}, f = 100\text{MHz}$
SWITCHING CHARACTERISTICS					
Turn-On Time	t_{off}	—	45	ns	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = -15\text{mA}$
Delay Time	t_d	—	10	ns	
Rise Time	t_r	—	40	ns	
Turn-Off Time	t_{off}	—	100	ns	$V_{CC} = -6.0\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$
Storage Time	t_s	—	80	ns	
Fall Time	t_f	—	30	ns	

Notes: 9. Short duration pulse test used to minimize self-heating effect.

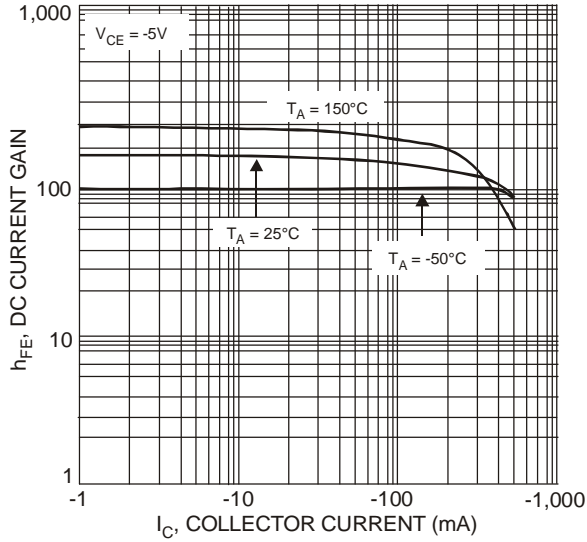


Fig. 1 Typical DC Current Gain vs. Collector Current

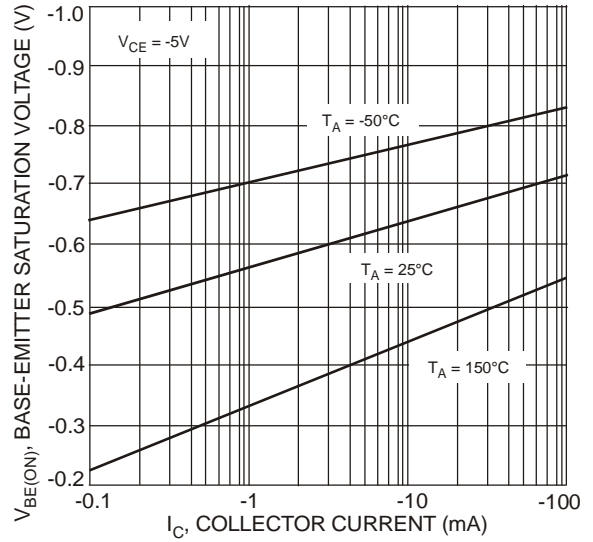


Fig. 2 Typical Base-Emitter Saturation Voltage vs. Collector Current

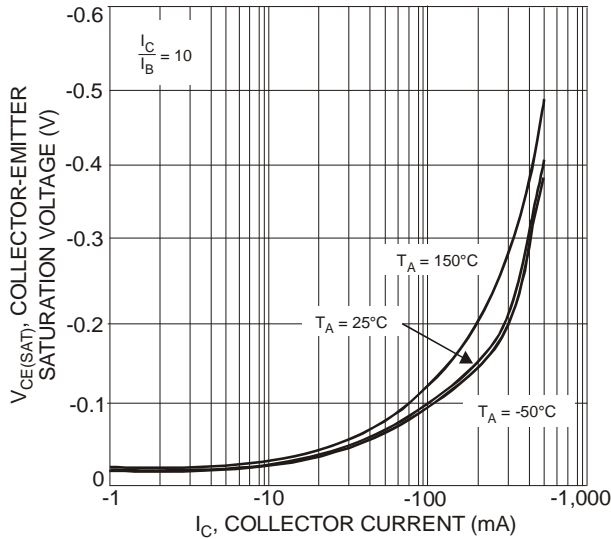


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

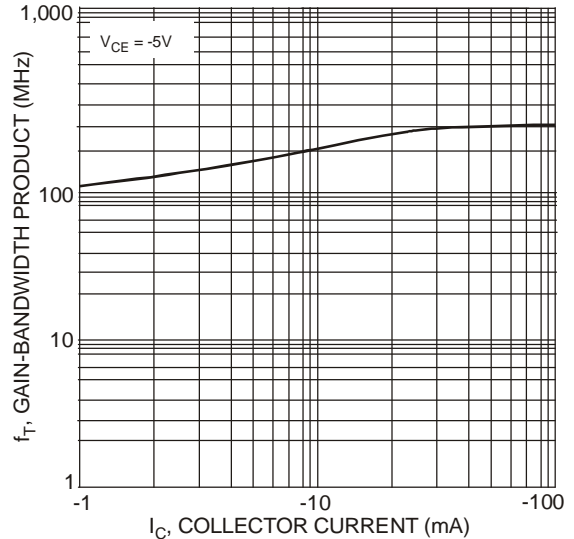


Fig. 4 Typical Gain-Bandwidth Product vs. Collector Current

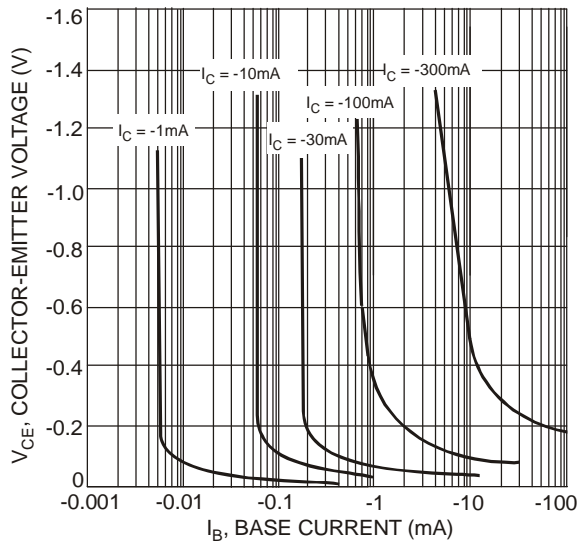


Fig. 5 Typical Collector Saturation Region

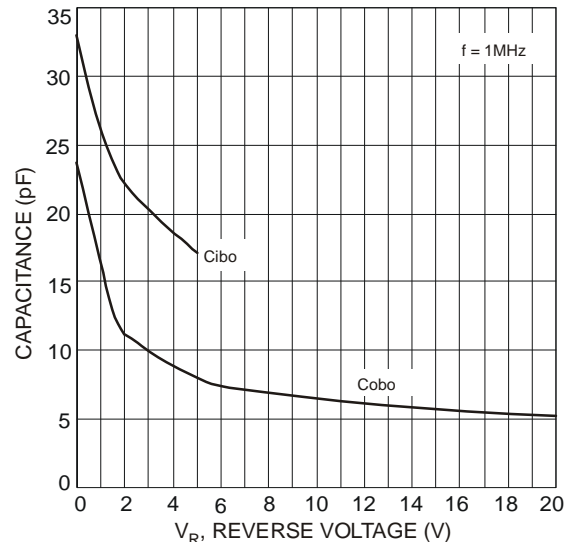
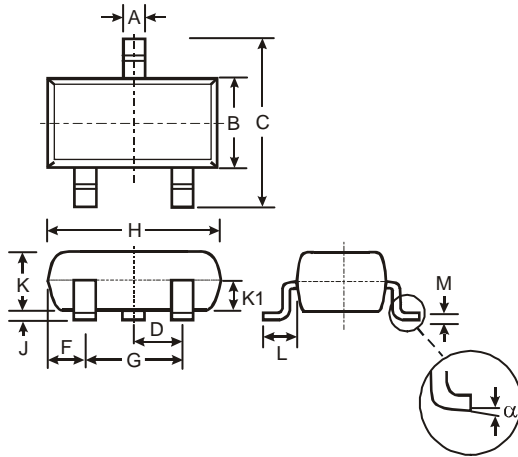


Fig. 6 Typical Capacitance Characteristics

Package Outline Dimensions

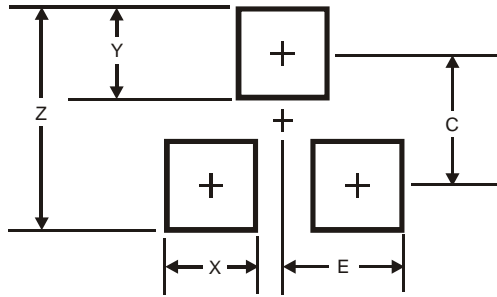
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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